

Title (en)  
METHOD FOR PRODUCING SCHOTTKY DIODES

Title (de)  
VERFAHREN ZUR HERSTELLUNG VON SCHOTTKY-DIODEN

Title (fr)  
PROCEDE DE PRODUCTION DE DIODES SCHOTTKY

Publication  
**EP 1145298 A3 20021120 (DE)**

Application  
**EP 99934481 A 19990511**

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Abstract (en)  
[origin: WO9962113A2] The invention relates to a method for producing Schottky diodes which comprise a guard ring (10) in the marginal area of the Schottky contact. Said guard ring (10) is produced by depositing a guard ring material (4) on the surface (8) of the semiconductor layer (2), said surface being provided with a structured masking layer (3) beforehand, and afterwards by siliconizing the guard ring material (4). The guard ring material (4) is a metal, especially a high barrier metal which, in particular, contains platinum.

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IPC 8 full level  
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